

Electric field measurement in irradiated silicon sensors by means of simulations and beam tests [Skype presentation]

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Beam test data and simulations can make accessible the electric field profile of silicon sensors. Different bulk materials, irradiation and annealing scenarios can be contrasted thanks to the charge profile technique (e.g.: T. Lari and C. Troncon, IEEE TNS, VOL. 53, NO. 5, OCTOBER 2006; V. Chiochia, IEEE TNS, VOL. 52, NO. 4, AUGUST 2005) High pointing resolution telescopes and detailed TCAD simulations are needed to complete this task. We will present the project for beam tests and simulations campaigns. In particular we will give all the organization details about the upcoming beamtest at SPS; moreover we will look for groups interested in measuring their samples on beam.

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